100 V, 3 A NPN high power bipolar transistor

11 September 2015

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61003PY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	90	150	mΩ
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	75	110	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	E	emitter		В
3	Е	emitter	[q]	- M
4	В	base	وققق	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	3,11123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61003NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61003NY	1003NAB

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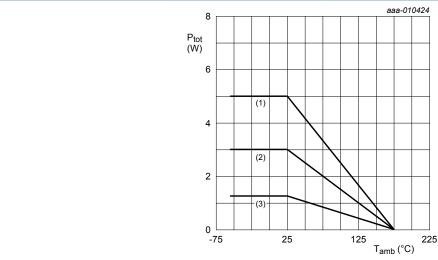
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	100	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB) single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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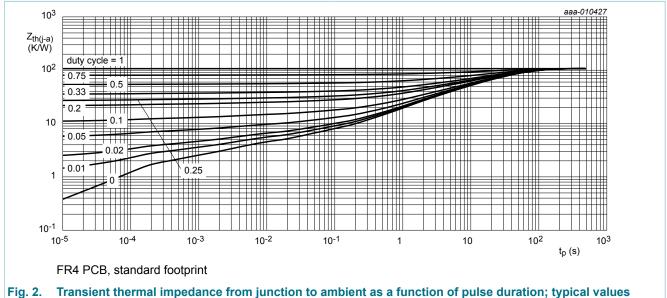
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Thermal characteristics

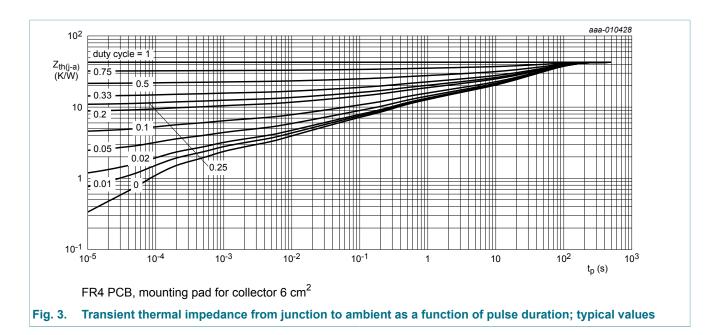
Thermal characteristics Table 6.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
() w)	thermal resistance		[1]	-	-	115	K/W
	from junction to		<u>[2]</u>	-	-	50	K/W
	ambient		[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard
- Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



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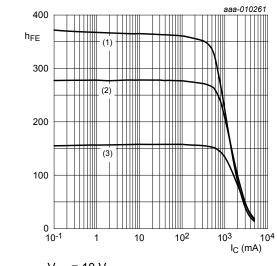
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 80 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	100	nA
	current	V_{CB} = 80 V; I_{E} = 0 A; T_{j} = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 80 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	150	250	-	
		V_{CE} = 10 V; I_{C} = 1 A; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	80	250	-	
		V_{CE} = 10 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pused	20	100	-	
		V_{CE} = 10 V; I_{C} = 3 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C; pulsed	10	40	-	
V _{CEsat} collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	90	150	mV	
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	225	330	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	90	150	mΩ
		$I_C = 3 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	75	110	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.86	1	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.1 A; T_{amb} = 25 °C	-	0.67	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	20	-	ns
t _r	rise time	I_{Boff} = -0.05 A; T_{amb} = 25 °C	-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF



 V_{CE} = 10 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

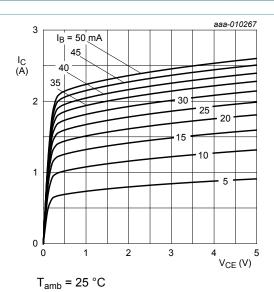
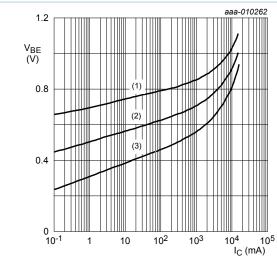


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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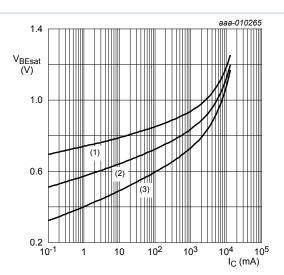
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



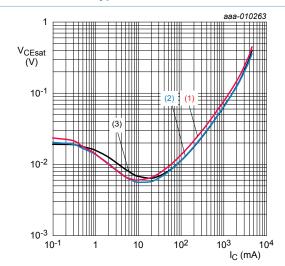
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



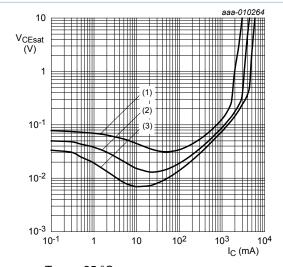
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



 T_{amb} = 25 °C

(1)
$$I_C/I_B = 50$$

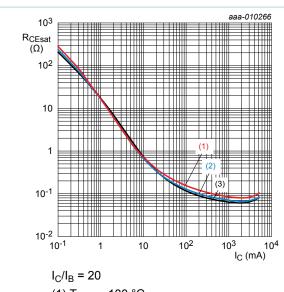
(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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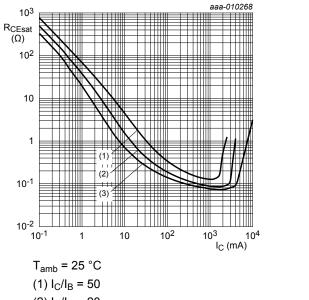


(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



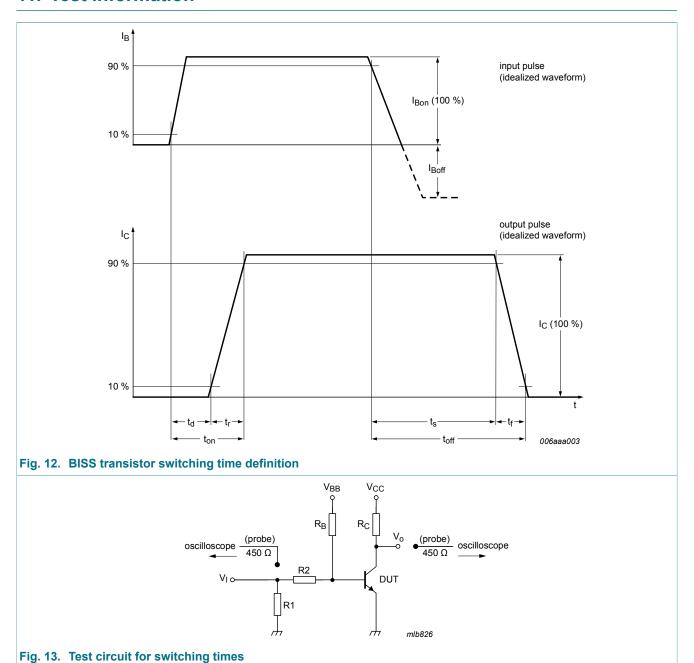
(2) $I_C/I_B = 20$

(3) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

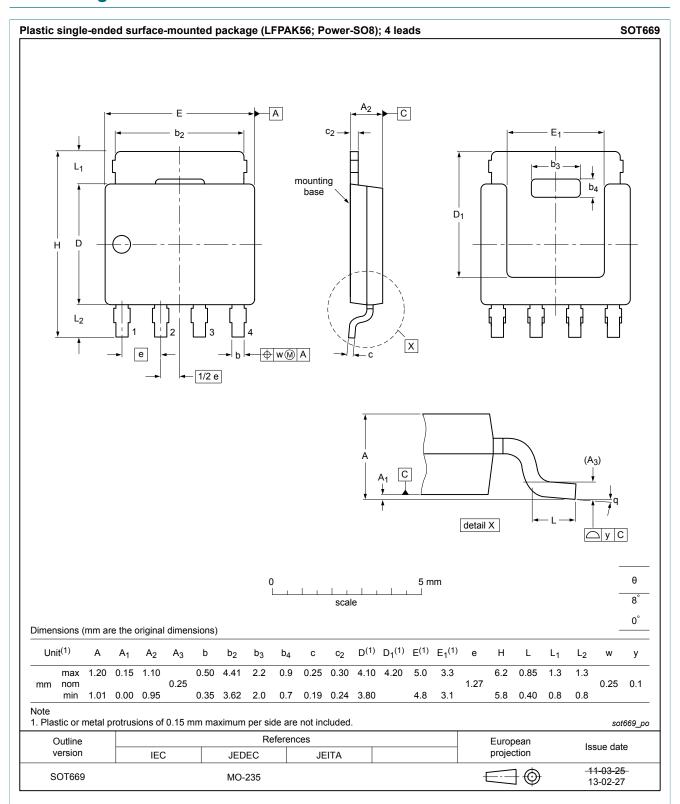


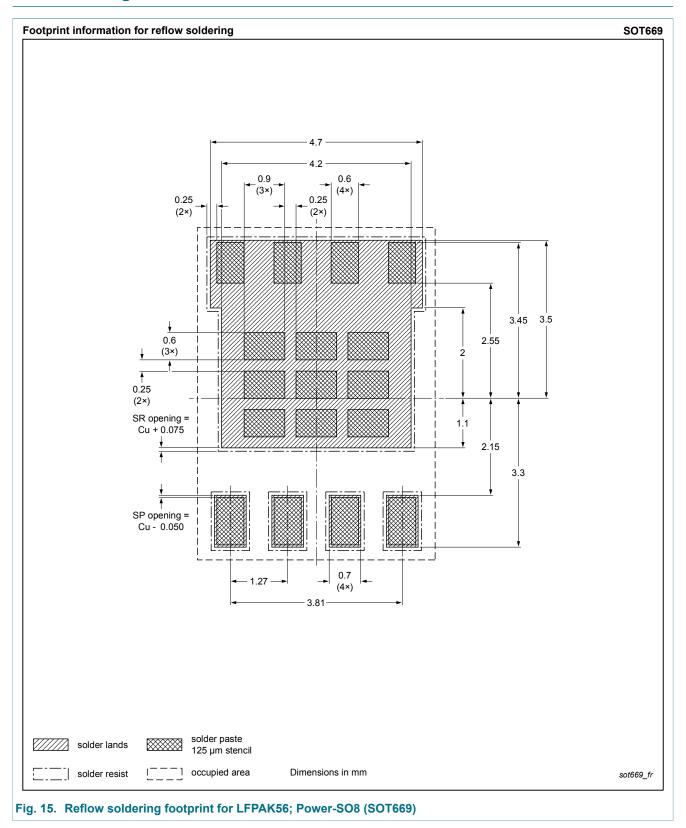
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering

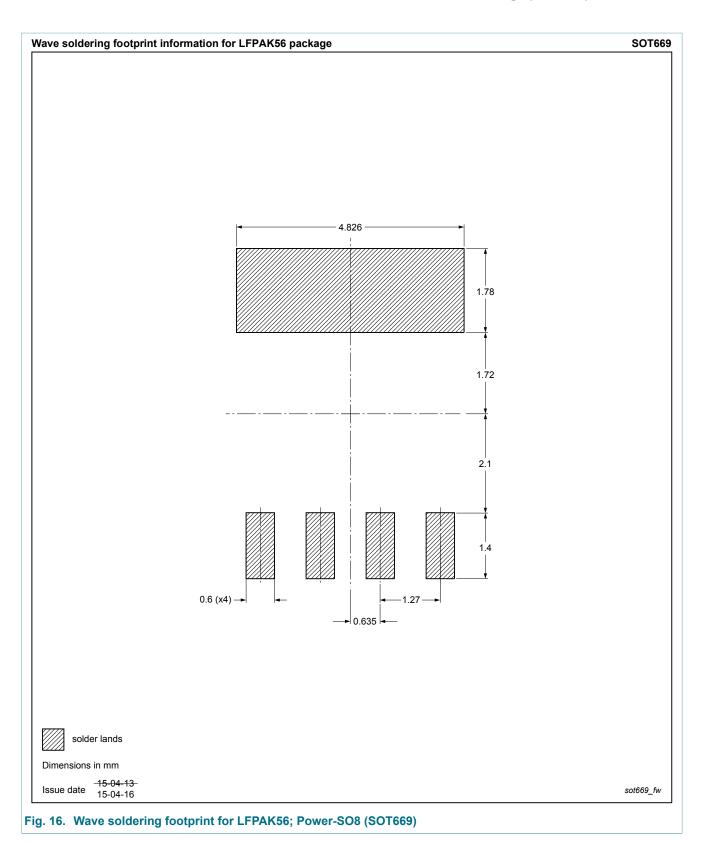


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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003NY v.4	20150911	Product data sheet	-	PHPT61003NY v.3
Modifications:	Editorial update of sUpdate of Figure 4	section 11. Test information	on	
PHPT61003NY v.3	20140203	Product data sheet	-	PHPT61003NY v.2
PHPT61003NY v.2	20131213	Product data sheet	-	PHPT61003NY v.1
PHPT61003NY v.1	20140113	Product data sheet	-	

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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